AMENDMENTS TO THE CLAIMS

Please amend the claims, as follows:

1. (Currently amended) An electrode for a p-type SiC, comprising a first electrode material, and a second electrode material of aluminum (Al), said first and second electrode materials exhibiting an eutectic reaction at a temperature of 600°C or lower, wherein a layer made of said first electrode material is in contact with a surface of the p-type SiC, said first electrode material comprising germanium (Ge).

2. (Canceled)

3. (Currently amended) An electrode for a p-type SiC according to ~~claim 2~~ claim 1, further comprising a third electrode material of titanium (Ti).

4. (Canceled)

5. (Previously presented) An electrode for a p-type SiC, comprising a first layer of germanium (Ge), and a second layer of aluminum (Al), wherein said first and second layers are formed successively on the p-type SiC and said first layer is in contact with a surface of the p-type SiC, the first layer and second layer exhibiting a eutectic reaction at a temperature of 600°C or lower.

6. (Previously Presented) An electrode for a p-type SiC according to claim 5, further comprising a third layer of titanium (Ti) formed between said first and second layers.

7. (Previously Presented) An SiC device including a p-type SiC, and an electrode for the p-type SiC defined in claim 1 and formed on said p-type SiC.

8. (Canceled)

9. (Previously Presented) An SiC device including a p-type SiC, and an electrode for the p-type SiC defined in claim 3 and formed on said p-type SiC.

10. (Canceled)

11. (Previously Presented) An SiC device including a p-type SiC, and an electrode for the p-type SiC defined in claim 5 and formed on said p-type SiC.

12. (Previously Presented) An SiC device including a p-type SiC, and an electrode for the p-type SiC defined in claim 6 and formed on said p-type SiC.

13-24. (Canceled)

25. (Previously Presented) An electrode for a p-type SiC according to claim 1, further comprising an ohmic junction formed between the p-type SiC and the first electrode material.

26. (Previously Presented) An electrode for a p-type SiC, comprising:

means for accelerating a eutectic reaction at a temperature of 600°C or lower;

first means for reducing contact resistivity; and

second means for reducing contact resistivity, wherein the first means for reducing contact resistivity comprises a different component than the second means for reducing contact resistivity.

27. (Previously Presented) An electrode for a p-type SiC according to claim 26, wherein the means for accelerating a eutectic reaction comprises a layer disposed on a surface of the p-type SiC.

28. (Previously Presented) An electrode for a p-type SiC according to claim 26, wherein the second means for reducing contact resistivity is disposed between the means for accelerating a eutectic reaction and the first means for reducing contact resistivity.

29. (Previously Presented) An electrode for a p-type SiC according to claim 26, further comprising an ohmic junction between the means for accelerating a eutectic reaction and a surface of the p-type SiC.

30. (Previously Presented) An electrode for a p-type SiC according to claim 26, wherein the means for accelerating the eutectic reaction further comprises means for solidifying a mixture of Ge, Al, and Ti at 600°C or lower.

31. (Previously Presented) An electrode for a p-type SiC according to claim 26, further comprising means for suppressing thermal damage to the electrode during heat treatment.

32. (Previously Presented) An electrode for a p-type SiC according to claim 29, further comprising means for increasing current flow through the ohmic junction.

33. (Currently amended) An electrode for a p-type SiC according to claim 1, wherein a thickness of said ~~first material~~ germanium is approximately 60 nm and a thickness of said aluminum is approximately 360 nm.

34. (Currently amended) An electrode for a p-type SiC according to claim 3, wherein a thickness of said germanium ~~material~~ is approximately 60 nm, a thickness of said aluminum is approximately 360 nm, and a thickness of said titanium is approximately 80 nm.